

Department of CSE

LAB REPORT

Course Code and Name: CSE251[Electronic Circuits]

Experiment no: 01

| Experiment name: I-V Characteristics and Modeling of Forward Conduction of a D Semester and Year: Fall-24 GROUP NO: 02 Name of Student: Course Instructor information: | |
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| Name of Student: Course Instructor information: | |
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| 2. (2022-3-60-188) | |
| 3. (2023-1-60-204) | |
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| Date of Report Submitted: Pre-Lab Marks: | |
| 11 November 2024 Post Lab Marks: | |
| TOTAL Marks: | |

Data sheet

CSE251 (Section-7)

Group-02

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Data Sheet:

| Measured Value of R (KΩ) | $I_D (mA) = V_R/R(K\Omega)$ | V _R (V) | V _D (V) | Vs |
|-----------------------------|-----------------------------|--------------------|--------------------|-------|
| | 0 | 0 | 0.487 | 0.1 |
| 0.97kn | 0 | 0 | 0.145 | 0.2 |
| | 0 | 0 | 0.21 | 0.3 |
| | 0 | 0 | 0.316 | 0.4 |
| | 0.18 | 0.018 | 0.437 | 0.5 |
| | 0.061 | 0.660 | 0.482 | 0.6 |
| | 0.107 | 0.105 | 0.504 | 0.7 |
| | 0.202 | 0.196 | 0.532 | 0.8 |
| | 0.204 | 0.285 | 0.549 | 0.9 |
| | 0.371 | 0.360 | 0.559 | 1 |
| | 0.689 | 0.669 | 0.589 | 1.3 |
| | 0.996 | 0-967 | 0.607 | 1.3 |
| | 1.145 | 1.111 | 0.614 | 1.8 |
| | 0 | 0 | 0.623 | . 2 |
| | 0 | 0 | 0.639 | 2.5 |
| | 2.362 | 2.291 | 0.649 | 3 |
| | 2.362 | 2.790 | 0.695 | 3.5 |
| | 3.397 | 3.296 | 0.668 | 4 |
| | 3.936 | 3.818 | 0.674 | 4.5 |
| | 4.924 | 4.202 | 0.681 | 5 |
| | 5.41 | 5.256 | 0.690 | 5 |
| | 6.465 | 6.272 | 0.608 | 7 |
| | 7.50 | 6.272 | 0.706 | 7 8 |
| | 8.548 | 8.202 | 0.711 | 9 |
| | 9.616 | 9-328 | 0.716 | 10 |
| | 11.65 | 11.305 | 0.728 | 12 |
| | 13.677 | 13.267 | 0.735 | |
| | 15.001 | 15.33 | 0.742 | 14 |
| | 15.804 | 17.326 | 6.748 | 16 |
| | 17.862 | 19.308 | 0.753 | 18 20 |
| | 19.905 | 20. 308 | 0.473 | 20 |

Post lab questions and solutions

1. Plot the I-V characteristics of the p-n junction diode in forward conduction. Label the axes appropriately and have them printed.

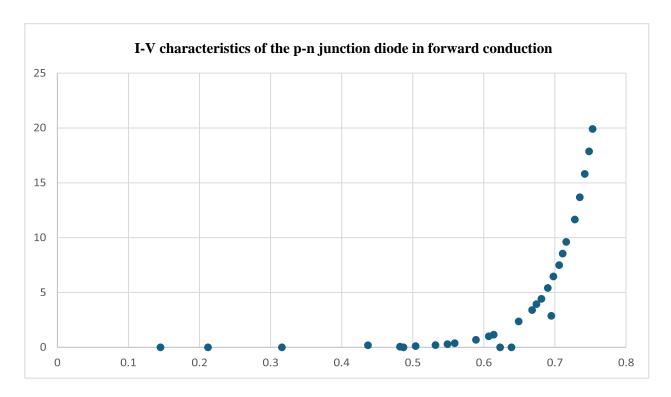


Figure-1

2. Use pencil to identify the points on your graph that are corresponding to ID1 = 2 mA and ID2 = 2.5 mA. Use these data points to calculate the diode parameters IS and n from the equation $ID = IS \exp [VD/nVT]$. Use VT = 0.0259V.

When, ID1 = 2mA then VD1 = 0.64 V

And ID2 = 2.5 mA then VD2 = 0.66 V

Now to find n we can use this equation, $VD2 - VD1 = nVT \ln(ID2 / ID1)$

=> n = VD2 - VD1 / VT ln(ID2 / ID1)

 $=> n = (0.66-0.64) / 0.0259 \ln(2.5 / 2)$

=> n = 3.46

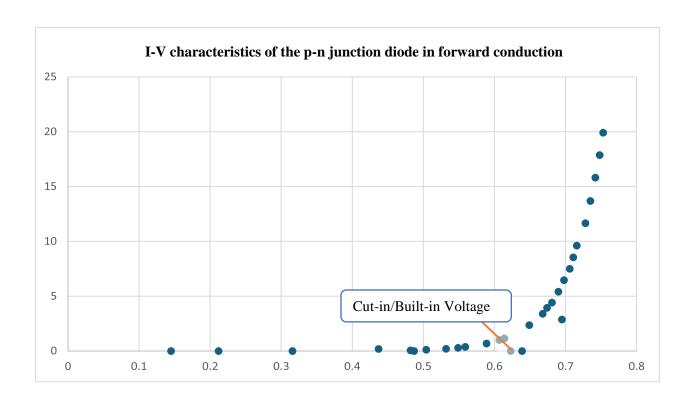
And, ID = IS e [VD1/nVT]

 \Rightarrow IS = ID / e [VD1/nVT]

$$=> IS = 2 / e^{(0.64/1.73 \times 0.0259)}$$

$$=> IS = 0.00125 \text{ mA}.$$

3. Determine the cut-in voltage from the printed graph by drawing extrapolated line with pencil.



From the graph, the cut-in or built-in voltage is $V_{DO} = 0.6V$

4. If the diode resistance for the piecewise linear model is defined as $1/rD = \partial ID/\partial VD = (ID2 - ID1)/(V_{D2} - V_{D1})$, calculate the value of r_D from the data points corresponding to I_{D1} =2mA and I_{D1} =2.5mA.

$$I_{\rm D1}=2.0~mA$$
 and $V_{\rm D1}=0.64V$

And for

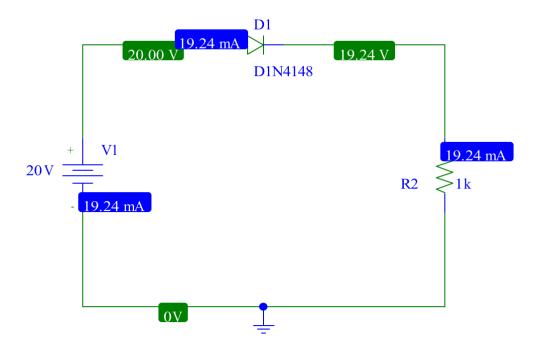
$$I_{D2} = 2.5 \text{mA}$$
 and $V_{D2} = 0.66 \text{V}$

We know,

$$r_D = (ID2 - IDI) / (VD2 - VDI)$$

$$r_D = 0.04 \ K\Omega$$

5. Simulate the circuit of Figure 1 for a DC bias (Vs) range of 0-5 volts using PSpice. Print the ID vs. VS and VD vs. VS plots generated by PSpice and attach them with your report.



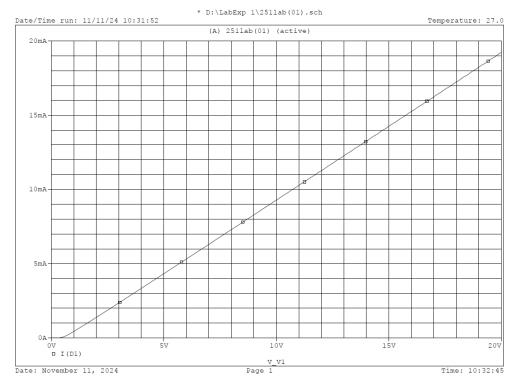


Figure: I_D vs V_S



Figure: V_D vs V_S

Conclusion:

From this lab, we have learned about the characteristics of diodes. From this experiment, we've learned that Diodes will prevent currents in reverse directions. From the I-V characteristics we know about forward, reverse and no bias concept. Our concept is increased about diode and I vs. V characteristics by doing this experiment. To do the experiment easily ohms law helps us. By using ohms law, we can easily find voltage and current. We can easily find the I-V characteristics by using Shockley ideal equation. We also use a piecewise linear model to understand the lab easily.